Product data sheet

1 General description

The BGU8063 also known as the BTS3001H, is a high-linearity bypass amplifier for wireless infrastructure applications, equipped with fast shutdown to support TDD systems. The LNA has a high input and output return loss and is designed to operate between 2.5 GHz and 5 GHz. It is housed in a 3 mm x 3 mm x 0.85 mm with 10 terminals, in a plastic thin small outline package. The LNA is ESD protected on all terminals.

2 Features and benefits

- Low noise performance: NF = 1.4 dB
- High-linearity performance: IP3_o = 34 dBm
- High-input return loss > 10 dB
- High-output return loss > 10 dB
- Unconditionally stable up to 20 GHz
- Small 10-terminal leadless package 3 mm x 3 mm x 0.85 mm
- ESD protection on all terminals
- · Moisture sensitivity level 1
- Fast shut down to support TDD systems
- +5 V single supply

3 Applications

- · Wireless infrastructure
- Low noise and high-linearity applications
- LTE, W-CDMA, CDMA, GSM
- General-purpose wireless applications
- TDD or FDD systems
- · Suitable for small cells



low-noise high-linearity amplifier

4 Quick reference data

Table 1. Quick reference data

f = 2500 MHz; V_{CC} = 5 V; T_{amb} = 25 °C; input and output 50 Ω ; unless otherwise specified. All RF parameters are measured on an application board with the circuit as shown in Figure 29 and components listed in Table 9 implemented. This board is optimized for f = 2500 MHz.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
I _{CC}	supply current	LNA enable; bypass off		-	75	90	mA
	LNA disable; bypass on		-	3	5	mA	
G _{ass}	associated gain	LNA enable; bypass off		17	18.5	20	dB
		LNA disable; bypass on		-2.2	-1.8	-	dB
NF	noise figure	LNA enable; bypass off	[1]	-	1.4	2.2	dB
P _{L(1dB)}	output power at 1 dB gain compression	LNA enable; bypass off		17.5	19	-	dBm
IP3 _O	output third-order intercept point	2-tone; tone spacing = 1 MHz; P	_ = 5 d	Bm pe	r tone		
		LNA enable; bypass off		31	34	-	dBm
		LNA disable; bypass on		-	43	-	dBm

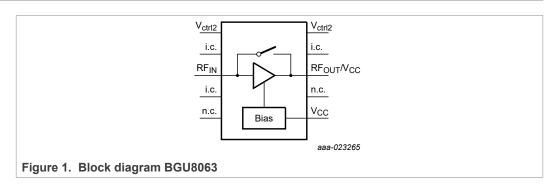
^[1] Connector and Printed-Circuit Board (PCB) losses have been de-embedded.

5 Ordering information

Table 2. Ordering information

Table 2. Ordering information					
Type number	orderable part	Package			
number		Name	Description	Version	
BGU8063	BGU8063J	HVSON10	plastic thermal enhanced very thin small outline package; no leads; 10 terminals; body 3 mm x 3 mm x 0.85 mm	SOT650-1	

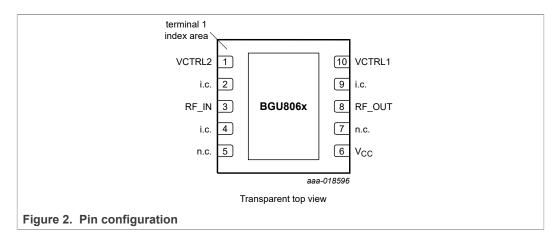
6 Block diagram



low-noise high-linearity amplifier

7 Pinning information

7.1 Pinning



7.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
VCTRL2	1	voltage control 2
i.c.	2, 4, 9	internally connected, can be grounded or left open in the application
RF_IN	3	RF input
n.c.	5	not connected
V _{CC}	6	supply voltage
n.c.	7	not connected
RF_OUT	8	RF output
VCTRL1	10	voltage control 1
GND	exposed die pad	ground

low-noise high-linearity amplifier

8 Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CC}	supply voltage			-	6	V
V _{i(CTRL1)}	input voltage on pin CTRL1			-	3.6	V
V _{i(CTRL2)}	input voltage on pin CTRL2			-	3.6	V
P _{i(RF)CW}	continuous waveform RF input power			-	20	dBm
T _{stg}	storage temperature			-40	150	°C
T _j	junction temperature			-	150	°C
Р	power dissipation	T _{case} ≤ 125 °C	[1]	-	510	mW
V _{ESD}	electrostatic discharge voltage	Human Body Model (HBM) according to ANSI/ESDA/JEDEC standard JS-001-2010		-	2	kV
		Charged Device Model (CDM); according to JEDEC standard 22-C101B		-	1	kV

^[1] Case is ground solder pad.

9 Recommended operating conditions

Table 5. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CC}	supply voltage		4.75	5	5.25	V
Z ₀	characteristic impedance		-	50	-	Ω

10 Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
$R_{\text{th(j-case)}}$	thermal resistance from junction to case	[1] [2]	55	K/W

Case is ground solder pad

11 Functional description

Table 7. Control truth table

 V_{CC} = 5 V; T_{amb} = 25 °C.

Control signal setting [1]		Mode of operation		
CTRL1	CTRL2	LNA	bypass	
LOW	HIGH	disable	on	
HIGH	HIGH	disable	on	
LOW	LOW	enable	off	
HIGH	LOW	disable	off	

^[1] A logic LOW is the result of an input voltage on that specific pin between -0.3 V and 0.7 V A logic HIGH is the result of an input voltage on the specific pin between 1.2 V and 3.6 V

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^[2] Thermal resistance measured using infrared measurement technique, device mounted on application board and placed in still air.

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12 Characteristics

Table 8. Characteristics

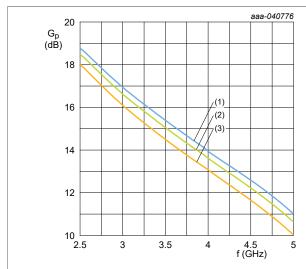
f = 2500 MHz; V_{CC} = 5 V; T_{amb} = 25 °C; input and output 50 Ω ; unless otherwise specified. All RF parameters are measured on an application board with the circuit as shown in Figure 29 and components listed in Table 9 implemented. This board is optimized for f = 2500 MHz.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
I _{CC}	supply current	LNA enable; bypass off		-	75	90	mA	
		LNA disable; bypass on		-	3	5	mA	
G _{ass}	associated gain	LNA enable; bypass off		17	18.5	20	dB	
		LNA disable; bypass on		-2.2	-1.8	-	dB	
G _{flat} gain flatness		within 100 MHz bandwidth; LNA enable; bypass off						
		2500 MHz ≤ f ≤ 4000 MHz		-	0.4	-	dB	
	3000 MHz ≤ f ≤ 3500 MHz		-	0.3	-	dB		
NF	noise figure	LNA enable; bypass off	[1]	-	1.4	2.2	dB	
ΔG	gain variation	2500 MHz ≤ f ≤ 4000 MHz		-	4.9	-	dB	
P _{L(1dB)}	output power at 1 dB gain compression	LNA enable; bypass off		17.5	19	-	dBm	
IP3 _O outpu	output third-order intercept	2-tone; tone spacing = 1 MHz; P _L = 5 dBm per tone						
	point	LNA enable; bypass off		31	34	-	dBm	
		LNA disable; bypass on		-	43	-	dBm	
RLin	input return loss	LNA enable; bypass off		-	-10	-	dB	
		LNA disable; bypass on		-	-20	-	dB	
RL _{out}	output return loss	LNA enable; bypass off		-	-10	-	dB	
		LNA disable; bypass on		-	-20	-	dB	
ISL	isolation	LNA disable; bypass off		-	30	-	dB	
		LNA enable; bypass off		-	25	-	dB	
t _{s(pon)}	power-on settling time	P _i = -20 dBm		-	0.5	-	μs	
t _{s(poff)}	power-off settling time	P _i = -20 dBm		-	0.1	-	μs	
K	Rollett stability factor	both ON-state and OFF-state up to f = 20 GHz		1	-	-	-	

^[1] Connector and Printed-Circuit Board (PCB) losses have been de-embedded.

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13 Graphics



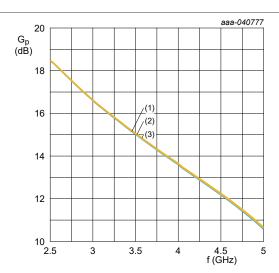
$$V_{CC} = 5 V$$

1.
$$T_{amb} = -40 \, ^{\circ}C$$

2.
$$T_{amb} = 25 \, ^{\circ}C$$

3.
$$T_{amb} = 95 \,^{\circ}C$$

Figure 3. Power gain as a function of frequency - Gain mode; typical values

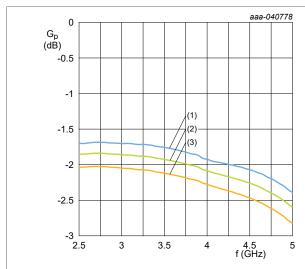


$$T_{amb} = 25 \, ^{\circ}C$$

1.
$$V_{CC} = 4.75 \text{ V}$$

3.
$$V_{CC} = 5.25 \text{ V}$$

Figure 4. Power gain as a function of frequency - Gain mode; typical values

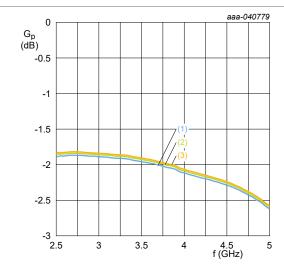


$$V_{CC} = 5 V$$

1.
$$T_{amb} = -40 \, ^{\circ}C$$

2.
$$T_{amb} = 25 \, ^{\circ}C$$

Figure 5. Power gain as a function of frequency - Bypass mode; typical values



1.
$$V_{CC} = 4.75 \text{ V}$$

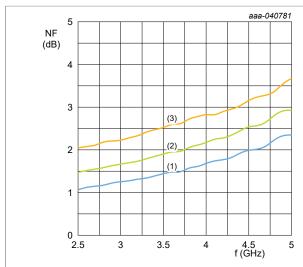
2.
$$V_{CC} = 5 V$$

3.
$$V_{CC} = 5.25 \text{ V}$$

Figure 6. Power gain as a function of frequency - Bypass mode; typical values

BGU8063

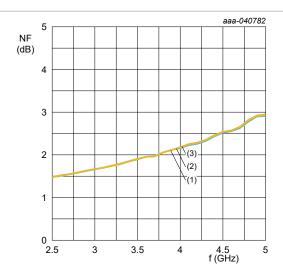
low-noise high-linearity amplifier



$$V_{CC} = 5 V$$

1.
$$T_{amb} = -40 \, ^{\circ}C$$

Figure 7. Noise figure as a function of frequency - Gain mode; typical values

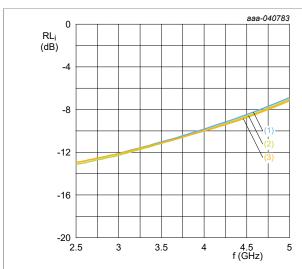


1.
$$V_{CC} = 4.75 \text{ V}$$

2.
$$V_{CC} = 5 V$$

3.
$$V_{CC} = 5.25 \text{ V}$$

Figure 8. Noise figure as a function of frequency - Gain mode; typical values



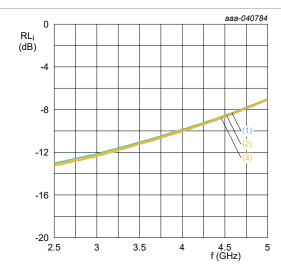
$$V_{CC} = 5 V$$

1.
$$T_{amb} = -40 \, ^{\circ}C$$

2.
$$T_{amb} = 25 \,^{\circ}C$$

3.
$$T_{amb} = 95 \, ^{\circ}C$$

Figure 9. Input return loss as a function of frequency - Gain mode; typical values



$$T_{amb}$$
 = 25 °C

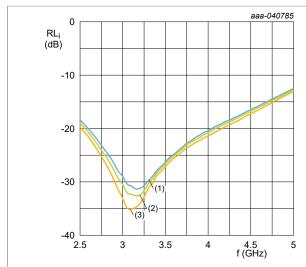
1.
$$V_{CC} = 4.75 \text{ V}$$

2.
$$V_{CC} = 5 V$$

3.
$$V_{CC} = 5.25 \text{ V}$$

Figure 10. Input return loss as a function of frequency - Gain mode; typical values

low-noise high-linearity amplifier

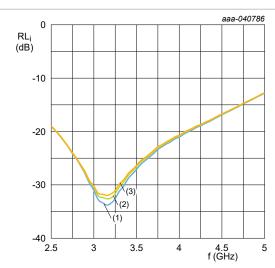


$$V_{CC} = 5 V$$

1.
$$T_{amb} = -40 \, ^{\circ}C$$

2.
$$T_{amb} = 25 \, ^{\circ}C$$

Figure 11. Input return loss as a function of frequency - Bypass mode; typical values

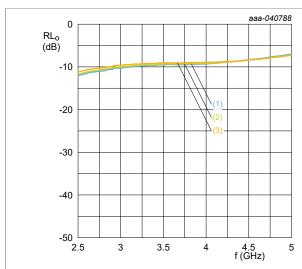


1.
$$V_{CC} = 4.75 \text{ V}$$

2.
$$V_{CC} = 5 V$$

3.
$$V_{CC} = 5.25 \text{ V}$$

Figure 12. Input return loss as a function of frequency - Bypass mode; typical values



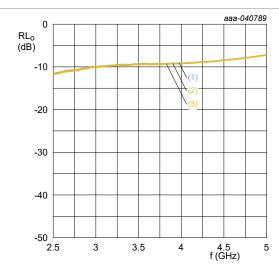
$$V_{CC} = 5 V$$

1.
$$T_{amb} = -40 \, ^{\circ}C$$

2.
$$T_{amb} = 25 \,^{\circ}C$$

3.
$$T_{amb} = 95 \, ^{\circ}C$$

Figure 13. Output return loss as a function of frequency - Gain mode; typical values



$$T_{amb}$$
 = 25 °C

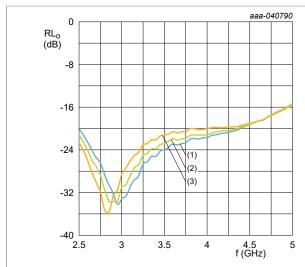
1.
$$V_{CC} = 4.75 \text{ V}$$

2.
$$V_{CC} = 5 V$$

3.
$$V_{CC} = 5.25 \text{ V}$$

Figure 14. Output return loss as a function of frequency - Gain mode; typical values

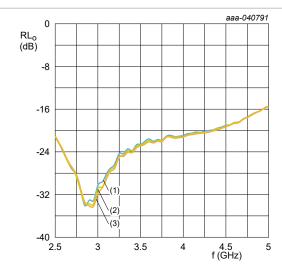
low-noise high-linearity amplifier



$$V_{CC} = 5 V$$

2.
$$T_{amb} = 25 \, ^{\circ}C$$

Figure 15. Output return loss as a function of frequency - Bypass mode; typical values

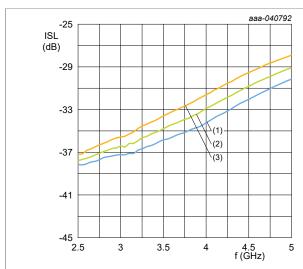


1.
$$V_{CC} = 4.75 \text{ V}$$

2.
$$V_{CC} = 5 V$$

3.
$$V_{CC} = 5.25 \text{ V}$$

Figure 16. Output return loss as a function of frequency - Bypass mode; typical values



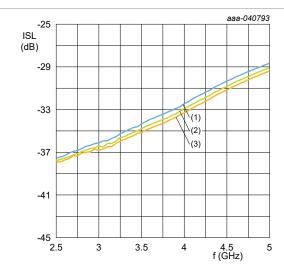
$$V_{CC}$$
 = 5 V

1.
$$T_{amb} = -40 \, ^{\circ}C$$

2.
$$T_{amb} = 25 \,^{\circ}C$$

3.
$$T_{amb} = 95 \, ^{\circ}C$$

Figure 17. Isolation as a function of frequency - Isolation mode; typical values



$$T_{amb}$$
 = 25 °C

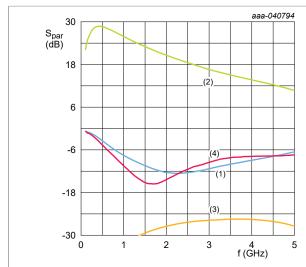
1.
$$V_{CC} = 4.75 \text{ V}$$

2.
$$V_{CC} = 5 V$$

3.
$$V_{CC} = 5.25 \text{ V}$$

Figure 18. Isolation as a function of frequency - Isolation mode; typical values

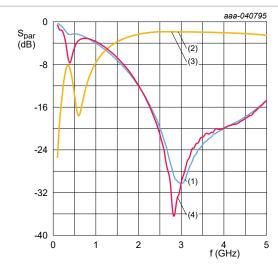
low-noise high-linearity amplifier



$$V_{CC}$$
 = 5 V; T_{amb} = 25 °C

- 1. S11
- 2. S21
- 3. S12
- 4. S22

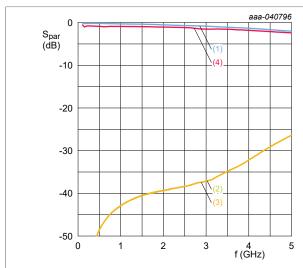
Figure 19. Wideband S-parameters as function of frequency - Gain mode; typical values



$$V_{CC}$$
 = 5 V; T_{amb} = 25 °C

- 1. S11
- 2. S21
- 3. S12
- 4. S22

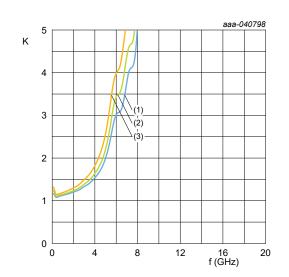
Figure 20. Wideband S-parameters as function of frequency - Bypass mode; typical values



 V_{CC} = 5 V; T_{amb} = 25 °C

- 1. S11
- 2. S21
- 3. S12
- 4. S22

Figure 21. Wideband S-parameters as function of frequency - Isolation mode; typical values

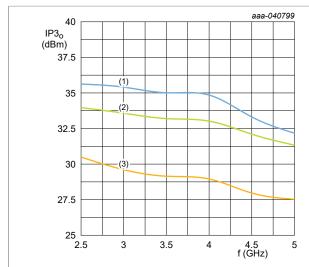


$$V_{CC} = 5 V$$

- 1. $T_{amb} = -40 \, ^{\circ}C$
- 2. T_{amb} = 25 °C
- 3. T_{amb} = 95 °C

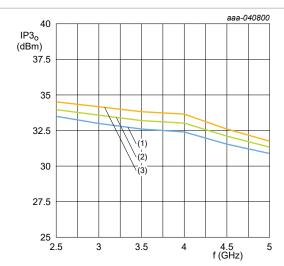
Figure 22. Rollett stability factor as function of frequency - Gain mode; typical values

low-noise high-linearity amplifier



$$V_{CC} = 5 V$$

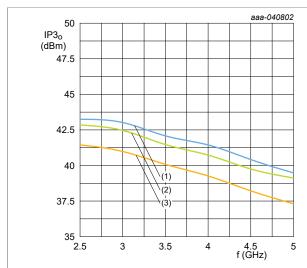
Figure 23. Output third-order intercept point as a function of frequency - Gain mode; typical values



1.
$$V_{CC} = 4.75 \text{ V}$$

3.
$$V_{CC} = 5.25 \text{ V}$$

Figure 24. Output third-order intercept point as a function of frequency - Gain mode; typical values



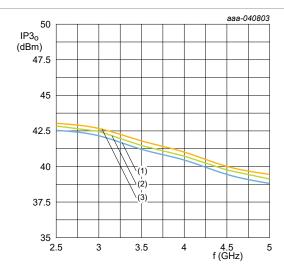
$$V_{CC} = 5 V$$

1.
$$T_{amb} = -40 \, ^{\circ}C$$

2.
$$T_{amb} = 25 \,^{\circ}C$$

3.
$$T_{amb} = 95 \, ^{\circ}C$$

Figure 25. Output third-order intercept point as a function of frequency - Bypass mode; typical values



$$T_{amb}$$
 = 25 °C

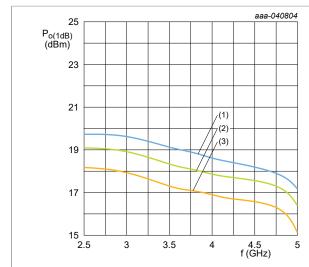
1.
$$V_{CC} = 4.75 \text{ V}$$

2.
$$V_{CC} = 5 V$$

3.
$$V_{CC} = 5.25 \text{ V}$$

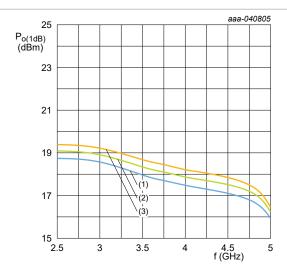
Figure 26. Output third-order intercept point as a function of frequency - Bypass mode; typical values

low-noise high-linearity amplifier



$$V_{CC} = 5 V$$

Figure 27. Output power at 1 dB gain compression as a functional of frequency - Gain mode; typical values



1.
$$V_{CC} = 4.75 \text{ V}$$

3.
$$V_{CC} = 5.25 \text{ V}$$

Figure 28. Output power at 1 dB gain compression as a functional of frequency - Gain mode; typical values

low-noise high-linearity amplifier

14 Application information

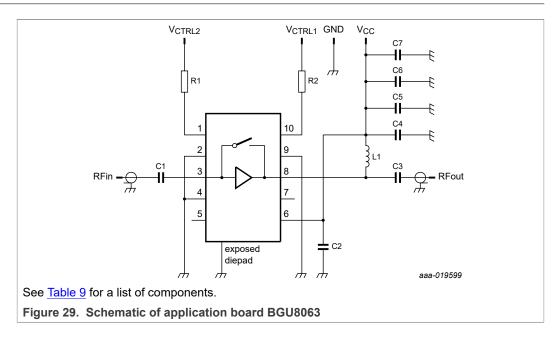
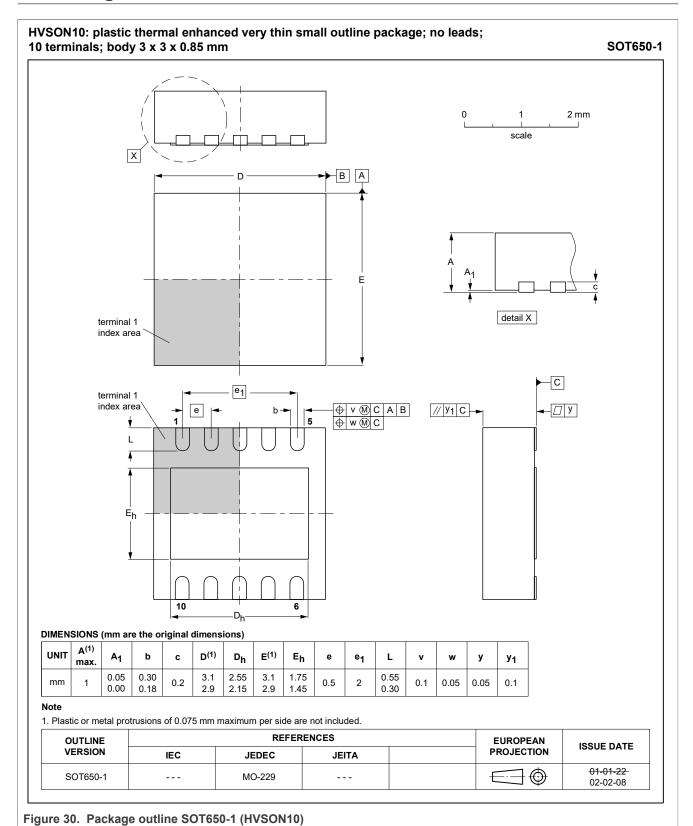


Table 9. List of components See Figure 29 for schematics.

Component	Description	Value	Remarks
C1	capacitor	100 nF	
C2, C3	capacitor	100 pF	
C4	capacitor	1 nF	
C5	capacitor	-	optional
C6	capacitor	10 nF	
C7	capacitor	1 μF	
L1	inductor	15 nH	
R1, R2	resistor	1 kΩ	

low-noise high-linearity amplifier

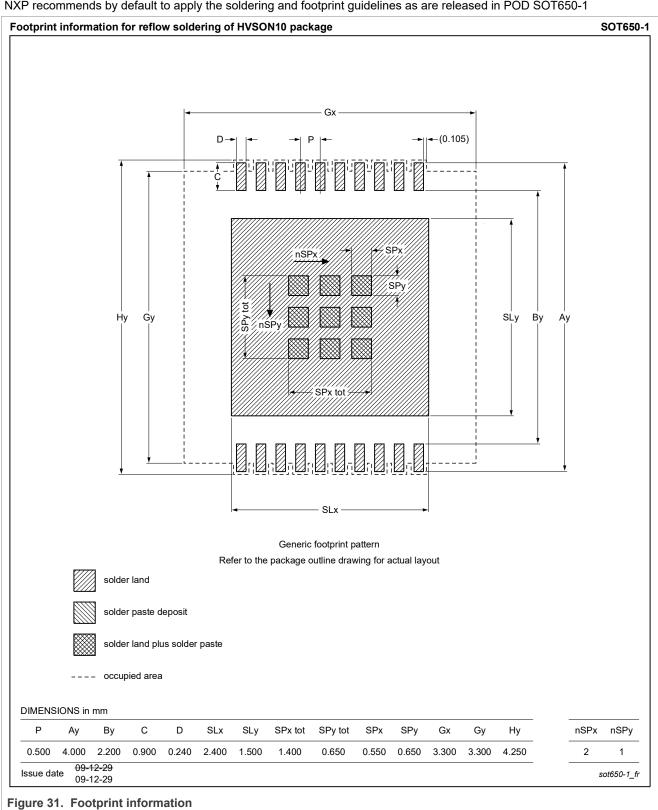
15 Package outline



low-noise high-linearity amplifier

15.1 Footprint and solder information

NXP recommends by default to apply the soldering and footprint guidelines as are released in POD SOT650-1



low-noise high-linearity amplifier

16 Abbreviations

Table 10. Abbreviations

Acronym	Description	
CDMA	code division multiple-access	
ESD	electroStatic discharge	
FDD	frequency-division duplexing	
GSM	global system for mobile communication	
LNA	low noise amplifier	
LTE	long-term evolution	
TDD	time-division duplexing	
W-CDMA	wideband code division multiple-access	

17 Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes			
BGU8063 v.3.1	20210210	Product data sheet	CIN	BGU8063 v.3			
modification	corrected typo wro	corrected typo wrong product name was mentioned BGU3063 instead of BGU8063					
BGU8063 v.3	20210127	Product data sheet	CIN	BGU8063 v.2			
modification	 changed frequency range in all graphics from 4 GHz to 5 GHz changed location of truth table from the Characteristics topic to the Functional description topic added solder footprint information added orderable part number to the Ordering information 						
BGU8063 v.2	20170127	Product data sheet	-	BGU8063 v.1			
modification	changed status to Product data sheet						
BGU8063v.1	20170112	Preliminary data sheet	-	-			

low-noise high-linearity amplifier

18 Legal information

18.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
- The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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